

2SD2358

Silicon NPN epitaxial planer type

For low-frequency output amplification

Complementary to 2SB1538

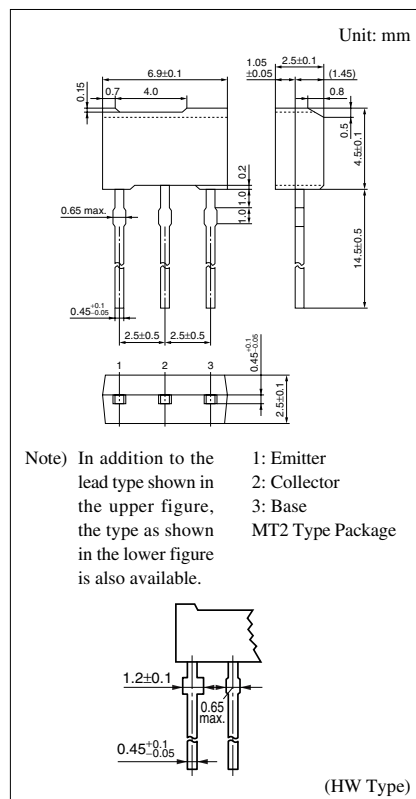
■ Features

- Low collector to emitter saturation voltage $V_{CE(sat)}$: < 0.15 V
- Allowing supply with the radial taping

■ Absolute Maximum Ratings $T_a = 25^\circ\text{C}$

Parameter	Symbol	Rating	Unit
Collector to base voltage	V_{CBO}	10	V
Collector to emitter voltage	V_{CEO}	10	V
Emitter to base voltage	V_{EBO}	5	V
Peak collector current	I_{CP}	1.2	A
Collector current	I_C	1	A
Collector power dissipation *	P_C	1	W
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature	T_{stg}	-55 to +150	$^\circ\text{C}$

Note) *: Printed circuit board: Copper foil area of 1 cm² or more, and the board thickness of 1.7 mm for the collector portion



■ Electrical Characteristics $T_a = 25^\circ\text{C} \pm 3^\circ\text{C}$

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Collector cutoff current	I_{CBO}	$V_{CB} = 7$ V, $I_E = 0$			1	μA
Collector to base voltage	V_{CBO}	$I_C = 10$ μA , $I_E = 0$	10			V
Collector to emitter voltage	V_{CEO}	$I_C = 1$ mA, $I_B = 0$	10			V
Emitter to base voltage	V_{EBO}	$I_E = 10$ μA , $I_C = 0$	5			V
Forward current transfer ratio	h_{FE}	$V_{CE} = 2$ V, $I_C = 100$ mA	200		800	
Collector to emitter saturation voltage	$V_{CE(sat)}$	$I_C = 500$ mA, $I_B = 20$ mA			0.15	V
Transition frequency	f_T	$V_{CB} = 5$ V, $I_E = -50$ mA, $f = 200$ MHz		120		MHz
Collector output capacitance	C_{ob}	$V_{CB} = 20$ V, $I_E = 0$, $f = 1$ MHz		30		pF